L Number	Hits	Search Text	DB	Time stamp		
- Number	HILS	118/719.ccls. and (chamber with pressure	USPAT;	2004/06/10 11:26		
	ľ	with higher with prevent)	US-PGPUB	2004/00/10 11.20		
	1	("20010040145").PN.	USPAT;	2003/02/26 10:13		
10	_	,	US-PGPUB			
-	196	156/345.24	USPAT;	2003/08/22 16:30		
			US-PGPUB			
ļ -	600	((156/345.24) or (156/345.51) or	USPAT;	2003/08/22 16:31		
}		(156/345.52) or (156/345.53)).CCLS.	US-PGPUB			
-	177	(((156/345.24) or (156/345.51) or	USPAT;	2004/06/09 19:43		
		(156/345.52) or (156/345.53)).CCLS.) and	US-PGPUB	1		
		(control\$3 with (substrate wafer target)				
	4	with temperature)		000010010017.14		
-	4	(((((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.) and	USPAT;	2003/08/22 17:14		
		(control\$3 with (substrate wafer target)	US-PGPUB			
		with temperature)) and ((high with				
		densit\$3) same (low with ion\$6))				
l _	728	(156/345.\$.CCLS.) and (control\$3 with	USPAT;	2004/06/09 19:44		
		(substrate wafer target) with temperature)	US-PGPUB	2001,00,05 25111		
_	142	(156/345.\$.CCLS.) and (control\$3 with	USPAT;	2004/06/09 19:44		
		(substrate wafer target) with temperature	US-PGPUB			
1		with etch\$3)				
-	166	(156/345.\$.CCLS.) and (control\$4 with	USPAT;	2004/06/09 19:46		
		(substrate wafer target) with temperature	US-PGPUB			
		with etch\$3)				
-	131	(156/345.\$.CCLS.) and (control\$4 with	USPAT;	2004/06/09 19:46		
		(substrate wafer target) with temperature	US-PGPUB			
	_	with during with (process\$3 treatm\$3))				
-	2	(156/345.\$.CCLS.) and (control\$4 with	USPAT;	2004/06/09 19:47		
		(substrate wafer target) with temperature	US-PGPUB			
		with during with (process\$3 treatm\$3) with damag\$3)				
1_	39	(control\$4 with (substrate wafer target)	USPAT;	2004/06/09 19:56		
-	23	with temperature with during with	US-PGPUB	2004/06/09 19:36		
		(process\$3 treatm\$3) with damag\$3)	03-16101			
-	0	(118/719.ccls. 156/345.31.ccls.	USPAT:	2004/06/09 20:00		
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	2001,00,03 20100		
		204/298.35.ccls.) and (156/345.24.ccls.				
1		156/345.27.ccls. 204/298.03.ccls.				
i		204/298.32.ccls.) and (control\$4 with	ļ			
		(substrate wafer workpiece) with				
		temperature with during with (process\$3				
1	_	treatm\$3) with damag\$3)				
- :	0	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:00		
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB			
		204/298.35.ccls.) and (156/345.24.ccls.				
		156/345.27.ccls. 204/298.03.ccls.				
		204/298.32.ccls.) and (control\$4 with (substrate wafer workpiece) with				
		temperature with damag\$3)				
_	79	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:00		
	.,	156/345.32.ccls. 204/298.25.ccls.	US-PGPUB	2001/00/03 20.00		
		204/298.35.ccls.) and (156/345.24.ccls.				
		156/345.27.ccls. 204/298.03.ccls.				
		204/298.32.ccls.)				
	24	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:11		
		156/345.32.ccls. 204/298.25.ccls.	US-PGPUB			
		204/298.35.ccls.) and (156/345.24.ccls.				
		156/345.27.ccls. 204/298.03.ccls.				
		204/298.32.ccls.) and (control\$4 with				
1.	0	temperature)		0004/06/00 00 :-		
1- 1	0	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls.	USPAT;	2004/06/09 20:12		
		204/298.35.ccls.) and (156/345.24.ccls.	US-PGPUB			
1		156/345.27.ccls. 204/298.03.ccls.				
1		204/298.32.ccls.) and (control\$4 with				
		temperature with magnet\$ with propert\$3)				
-	1	(118/719.ccls. 156/345.31.ccls.	USPAT;	2004/06/09 20:12		
	_	156/345.32.ccls. 204/298.25.ccls.	US-PGPUB			
		204/298.35.ccls.) and (control\$4 with				
		temperature with magnet\$ with propert\$3)				
Glade William Glade 2 47 co NV						

	3	(156/345.24.ccls. 156/345.27.ccls.	USPAT:	2004/06/09 20:13
i	,	204/298.03.ccls. 204/298.32.ccls.) and	US-PGPUB	2004/06/09 20:13
	İ		US-PGPUB	i
١.		(control\$4 with temperature with magnet\$ with propert\$3)		
1	133	(control\$4 with temperature with magnet\$	EPO: JPO:	2004/06/09 20:13
7	133	with propert\$3)	DERWENT	2004/06/09 20:13
l <u>-</u>	2		EPO; JPO;	2004/06/09 20:14
l	_	with propert\$3 with (during) with (treat\$4	DERWENT	2004/00/09 20:14
		process\$4))	DERWEINT	
l –	1 11		USPAT:	2004/06/09 20:20
		with propert\$3 with (during) with (treat\$4	US-PGPUB	2001,00,03 20120
		process\$4))		
-	65	(control\$4 with temperature with magnet\$	USPAT;	2004/06/09 20:20
		with propert\$3 with (treat\$4 process\$4))	US-PGPUB	
i –	65	(control\$4 with temperature with magnet\$	USPAT;	2004/06/09 20:21
	i	with propert\$3 with (treat\$4 process\$4))	US-PGPUB	
-	24	(control\$4 with temperature with magnet\$	EPO; JPO;	2004/06/09 20:21
		with propert\$3 with (treat\$4 process\$4))	DERWENT	
-	788	(156/345.\$.ccls. 118/715/733.\$.ccls.) and	USPAT;	2004/06/10 11:27
İ		((control\$4 with temperature) with	US-PGPUB	
	1	(substrate wafer workpiece))	İ	i
-	177		USPAT;	2004/06/10 11:27
		((control\$4 with temperature) with	US-PGPUB	
	13	(substrate wafer workpiece) with (during))		
[-	13	(156/345.\$.ccls. 118/715/733.\$.ccls.) and	USPAT;	2004/06/10 13:13
	1	((control\$4 adj temperature) adj (substrate wafer workpiece) adj (during))	US-PGPUB	!
_	22	(156/345.\$.ccls.) and ((low adj	USPAT;	2004/06/10 13:14
	""	temperature) adj (etch\$3))	US-PGPUB	2004/06/10 13:14
_	10	("5571366" "5572366" "5645683"	USPAT	2004/06/10 13:17
	1	"5695564" "5695654" "5700734"	OSENI	2004/00/10 13:1/
		"5756401" "6008139" "6046116"		1
		"6087264").PN.		
-	18		USPAT:	2004/06/10 13:22
l		same (low adj ion adj energy) same (high	US-PGPUB	-551, 55, 15 15.22
		adj density))		